

STRUCTURE Silicon Monolithic Integrated Circuit

NAME OF PRODUCT DC-AC Inverter Control IC

TYPE BD9884FV

FUNCTION • 2ch control with Half-bridge

· Lamp current and voltage sense feed back control

• Sequencing easily achieved with Soft Start Control

• Short circuit protection with Timer Latch

· Under Voltage Lock Out

• Short circuit protection with over voltage

• Mode-selectable the operating or stand-by mode by stand-by pin

2ch BURST mode selectivity in-phase or reversed phase

- Synchronous operating the other BD9884FV IC's

### OAbsolute Maximum Ratings ( $Ta = 25^{\circ}C$ )

Parameter	Symbol	Limits	Unit
Supply Voltage	Vcc	12	V
Operating Temperature Range	Topr	-35 <b>~</b> +85	°C
Storage Temperature Range	Tstg	−55 <b>~</b> +125	°C
Power Dissipation	Pd	850*	mW
Maximum Junction Temperature	Tjmax	+125	င္

<sup>\*</sup>Pd derated at 8.5mW/°C for temperature above Ta = 25°C (When mounted on a PCB 70.0mm $\times$ 70.0mm $\times$ 1.6mm)

#### ORecommended operating condition

Parameter	Symbol	Limits	Unit
Supply voltage	Vcc	5.0~11.0	V
CT oscillation frequency	fcT	20~150	kHz
BCT oscillation frequency	fвст	0.05~1.00	kHz

Status of this document

The Japanese version of this document is the official specification.

Please use the translation version of this document as a reference to expedite understanding of the official version.

If these is any uncertainty in translation version of this document, official version takes priority.



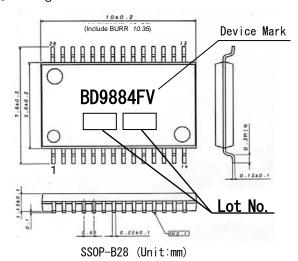
OElectric Characteristics (Ta=25°C, VCC=7V)

Electric Characteristics	(1a=25 C, V	<u>((=/v)</u>				
Parameter	Symbol		Limits	I MAY	Unit	Conditions
(/WHOLE DEVLOES)		MIN.	TYP.	MAX.		
((WHOLE DEVICE))	11		0.0	17.0	T	OT 0 5V
Operating current	lcc1	+ -	9.0	17. 0 10	mA	CT=0. 5V
Stand-by current ((OVER VOLTAGE DETECT))	Icc2		4	10	μA	
FB over voltage detect voltage	Vovf	2. 70	3. 00	3. 30	l v	T
((STAND BY CONTROL))	VOVI	2. 70	3.00	3. 30	V	
Stand-by voltage H1	T		I	1	1	
(BURST mode in reverse phase)	VstH1	2. 4	_	VCC	٧	System ON
Stand-by voltage H2						
(BURST mode in phase)	VstH2	1.4	_	1. 8	٧	System ON
Stand-by voltage L	VstL	-0. 3	_	0. 5	٧	System OFF
Stand-by hysteresis	⊿Vst	0. 10	0. 25	0. 40	V	-,
((TIMER LATCH))						
Timer Latch voltage	Vcp	1.8	2. 0	2. 2	V	
Timer Latch current	Icp	0. 5	1. 0	1. 5	μΑ	
((OSC BLOCK))	· · · · · · · · · · · · · · · · · · ·	-1	I.			1
OSC constant current	ICT	1. 35/RT	1. 5/RT	1. 65/RT	Α	
OSC Max voltage	VoscH	1.8	2. 0	2. 2	٧	fCT=60kHz
3	VoscL	0.3	0. 5	0. 7	٧	fCT=60kHz
OSC Min voltage					ļ	
MAX DUTY	MAXDUTY	44	46. 5	49	%	fCT=60kHz
Soft start current	Iss	1.0	2. 0	3. 0	μA	
IS COMP detect Voltage	Visc	0. 45	0. 60	0. 75	V	
SS COMP detect voltage	Vss	2. 0	2. 2	2. 4	V	
SRT ON resistance	RSRT	_	200	400	Ω	
((UVLO BLOCK))	T		1			
Operating voltage	VuvloH	4. 100	4. 300	4. 500	٧	
Lock out voltage	VuvloL	3. 900	4. 100	4. 300	V	
Operating voltage (External UVLO)	Vuv lo1	1. 900	2. 000	2. 100	٧	
Lock out voltage (External UVLO)	Vuv I o2	2. 100	2. 200	2. 300	V	
((FEED BACK BLOCK))	,	1	1	_	1	
IS threshold voltage	Vis	1. 220	1. 250	1. 280	V	
VS threshold voltage	Vvs	1. 220	1. 250	1. 280	٧	
IS source current 1	lis1	_	_	1.5	μA	DUTY=2. OV
IS source current 2	lis2	13. 0	20. 0	27. 0	μA	DUTY=0V、IS=0.5V
VS source current	lvs	_	_	1.0	μA	
((OUTPUT BLOCK))						
Pch output voltage H	VoutPH	VCC-0. 3	VCC-0. 1	_	V	
Nch output voltage H	VoutNH	VCC-0. 3	VCC-0. 1	_	V	
Pch output voltage L	VoutPL	_	0. 1	0. 3	V	
Nch output voltage L	VoutNL	_	0.1	0.3	V	
Pch output sink resistance	RsinkP	_	8	16	Ω	Isink = 10mA
Pch output source resistance	RsourceP	_	10	20	Ω	Isource = 10mA
Nch output sink resistance	RsinkN	_	8	16	Ω	Isink = 10mA
Nch output source resistance	RsourceN	_	10	20	Ω	Isource = 10mA
((BURST MODE BLOCK))	T	1	ı	,		
BOSC Max voltage	VburH	1. 92	2. 0	2. 08	V	fBCT=0. 3kHz
BOSC Min Voltage	VburL	0.4	0.5	0.6	٧	fBCT=0. 3kHz
BOSC constant current	IBCT	1. 35/BRT	1. 5/BRT	1. 65/BRT	Α	
((REG BLOCK))	1	<u> </u>	<u>'</u>	1 '	1	I
	VDEO	2 000	2 100	0 100	W	
REG output voltage	VREG	3. 038	3. 100	3. 162	V	
REG source current VREF voltage	IREG	5. 0	1 250	1 200	mA V	<u> </u>
	Vref	1. 220	1. 250	1. 280	Į V	
((COMP BLOCK))  Over voltage detect	VCOMPH	2. 20	2. 5	2 00	V	
Under voltage detect	VCOMPH	0. 590	0. 640	2. 80 0. 690	V	
((PROTECT CLOCK))	VOUMPL	0. 590	U. 04U	0. 090	_ V	
	VDH	0.0	2 1	2.0	l v	
Normal output voltage	VPH	2. 9	3.1	3.3	V	<u> </u>
Protect output voltage	VPL	_	_	0. 5	V	1

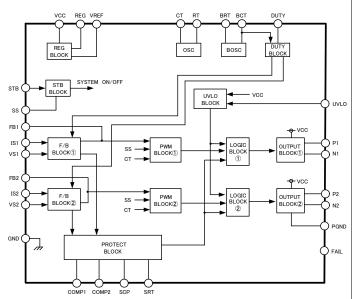
(This product is not designed for normal operation with in a radio active environment.)



### OPackage Dimensions



# **OBlock Diagram**



# OPin Description

Pin No.	Pin Name	Function	
1	DUTY	Control PWM mode and BURST mode	
2	BRT	External resistor from BRT to GND for adjusting the BURST triangle oscillator	
3	ВСТ	External capacitor from BCT to GND for adjusting the BURST triangle oscillator	
4	RT	External resistor from SRT to RT for adjusting the triangle oscillator	
5	SRT	External resistor from SRT to RT for adjusting the triangle oscillator	
6	СТ	External capacitor from CT to GND for adjusting the triangle oscillator	
7	GND	GROUND	
8	FB1	Error amplifier output①	
9	IS1	Error amplifier input①	
10	VS1	Error amplifier input②	
11	FB2	Error amplifier output②	
12	182	Error amplifier input③	
13	VS2	Error amplifier input4	
14	VREF	Reference voltage for ISNECE, VSENCE error amplifier	
15	FAIL	Protect clock output	
16	STB	Stand-by switch	
17	COMP1	Under, over voltage detect for 1ch	
18	COMP2	Under, over voltage detect for 2ch	
19	UVLO	External Under Voltage Lock OUT	
20	REG	Internal regulator output	
21	SS	External capacitor from SS to GND for Soft Start Control	
22	SCP	External capacitor from SCP to GND for Timer Latch	
23	P2	FET driver for 2ch	
24	N2	FET driver for 2ch	
25	PGND	Ground for FET drivers	
26	N1	FET driver for 1ch	
27	P1	FET driver for 1ch	
28	VCC	Supply voltage input	



#### **ONOTE FOR USE**

- 1. When designing the external circuit, including adequate margins for variation between external devices and the IC. Use adequate margins for steady state and transient characteristics.
- 2. Recommended Operating Range

The circuit functionality is guaranteed within of ambient temperature operation range as long as it is within recommended operating range. The standard electrical characteristic values cannot be guaranteed at other voltages in the operating ranges, however, the variation will be small.

3. Mounting Failures

Mounting failures, such as misdirection or miscounts, may harm the device.

4. Electromagnetic Fields

A strong electromagnetic field may cause the IC to malfunction.

- 5. The GND pin should be the location within  $\pm 0.3V$  compared with the PGND pin
- 6. BD9884FV has the short circuit protection with Thermal Shut Down System. When STB or Vcc pin re-supplied, They enables to cancel the latch. If It rise the temperature of the chip more than 170°C (TYP), It make the external FET OFF
- 7. Absolute maximum ratings are those values that, if exceeded, may cause the life of a device to become significantly shortened.
  Moreover, the exact failure mode caused by short or open is not defined. Physical countermeasures, such as a fuse, need to be considered when using a device beyond its maximum ratings.
- 8. About the external FET, the parasitic Capacitor may cause the gate voltage to change, when the drain voltage is switching.

  Make sure to leave adequate margin for this IC variation.
- 9. On operating Slow Start Control (SS is less than 2.2V), It does not operate Timer Latch.
- 1 O. By STB voltage, BD9884FV is changed to 3 states. Therefore, do not input STB pin voltage between one state and the other state  $(0.5 \sim 1.4 \text{V}, 1.8 \sim 2.4 \text{V})$ .
- 1 1. The pin connected a connector need to connect to the resistor for electrical surge destruction.
- 1 2. This IC is a monolithic IC which (as shown is Fig-1)has P\* substrate and between the various pins. A P-N junction is formed from this P layer of each pin. For example, the relation between each potential is as follows,
  - O (When GND > PinB and GND > PinA, the P-N junction operates as a parasitic diode.)
  - O(When PinB > GND > PinA, the P-N junction operates as a parasitic transistor.)

Parasitic diodes can occur inevitably in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits as well as operation faults and physical damage. Accordingly you must not use methods by which parasitic diodes operate, such as applying a voltage that is lower than the GND (P substrate) voltage to an input pin.

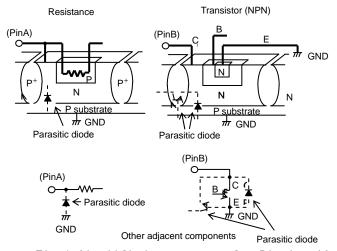


Fig-1 Simplified structure of a Bipolar IC

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